

N-channel TrenchMOS intermediate level FET Rev. 1 — 18 August 2010

Product data sheet

1. **Product profile**

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for intermediate level gate drive sources

1.3 Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control

1.4 Quick reference data

Table 1 Quick reference data

- Suitable for thermally demanding environments due to 175 °C rating
- Start-Stop micro-hybrid applications

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- Transmission control
- Ultra high performance power switching

| Table 1. | Quick reference | uala | | | | | |
|-------------------|--|--|------------|-----|-----|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 40 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u> | <u>[1]</u> | - | - | 120 | A |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | | - | - | 306 | W |
| Static cha | racteristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u> | | - | 1.6 | 1.9 | mΩ |

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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|--|---|-----|-----|------|------|
| Avalanch | e ruggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | $ \begin{split} I_D &= 120 \text{ A}; \text{V}_{\text{sup}} \leq 40 \text{ V}; \\ \text{R}_{\text{GS}} &= 50 \Omega; \text{V}_{\text{GS}} = 10 \text{ V}; \\ \text{T}_{j(\text{init})} &= 25 ^{\circ}\text{C}; \text{ unclamped} \end{split} $ | - | - | 1.02 | J |
| Dynamic | characteristics | | | | | |
| Q _{GD} | gate-drain charge | $I_D = 25 \text{ A}; V_{DS} = 32 \text{ V};$ $V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure } 13}{\text{Figure } 14};$ $\text{see } \frac{\text{Figure } 14}{\text{Figure } 14}$ | - | 72 | - | nC |

[1] Continuous current is limited by package.

Pinning information 2.

| Table 2. | Pinning | information | | |
|----------|---------|-----------------------------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | G | gate | | _ |
| 2 | D | Drain | mb | D |
| 3 | S | source | | |
| mb | D | mounting base; connected to drain | | mbb076 S |
| | | | SOT404 (D2PAK) | |

Ordering information 3.

| Table 3. Ordering information | | | | | |
|-------------------------------|---------|--|---------|--|--|
| Type number | Package | | | | |
| | Name | Description | Version | | |
| BUK661R9-40C | D2PAK | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 | | |

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|---|--|------------------|-----|------|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | 40 | V |
| V _{GS} | gate-source voltage | Pulsed | <u>[1]</u> | -20 | 20 | V |
| | | DC | [2] | -16 | 16 | V |
| I _D | drain current | $T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{1}$ | [3] | - | 120 | А |
| | | T_{mb} = 100 °C; V_{GS} = 10 V; see Figure 1 | [3] | - | 120 | А |
| I _{DM} | peak drain current | $T_{mb} = 25 \text{ °C; } t_p \le 10 \mu\text{s; pulsed;}$ see <u>Figure 3</u> | | - | 1107 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | | - | 306 | W |
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| Tj | junction temperature | | | -55 | 175 | °C |
| Source-drain | diode | | | | | |
| I _S | source current | T _{mb} = 25 °C | [3] | - | 120 | А |
| I _{SM} | peak source current | $t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$ | | - | 1107 | А |
| Avalanche rug | ggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I_D = 120 A; $V_{sup} \le 40$ V; $R_{GS} = 50$ Ω; $V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; unclamped | | - | 1.02 | J |
| E _{DS(AL)R} | repetitive drain-source avalanche energy | | <u>[4][5][6]</u> | - | - | J |

[1] Accumulated pulse duration not to exceed 5mins.

[2] -16V accumulated duration not to exceed 168 hrs

[3] Continuous current is limited by package.

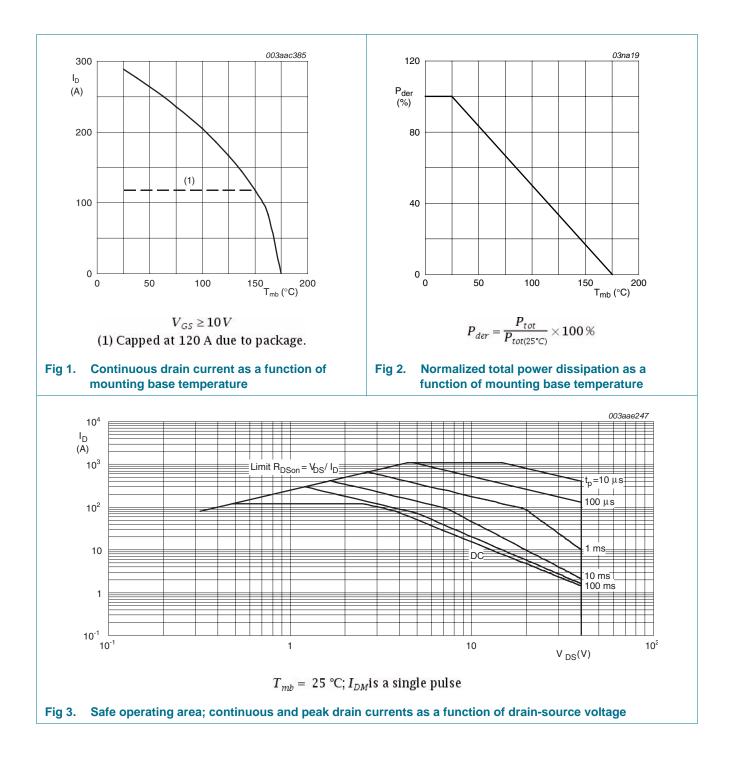
[4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[5] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[6] Refer to application note AN10273 for further information.

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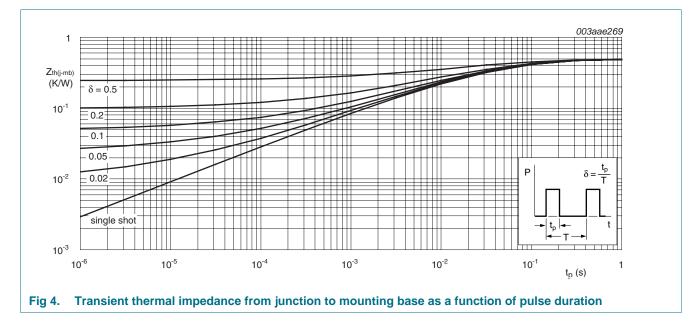
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5. Thermal characteristics

| Table 5. | Thermal characteristics | | | | | |
|-----------------------|---|----------------------|-----|-----|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| R _{th(j-mb)} | thermal resistance from junction to mounting base | see Figure 4 | - | - | 0.49 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | vertical in free air | - | 60 | - | K/W |



et

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6. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------------------------|-------------------------------------|--|-----|------|------|------|
| Static chara | cteristics | | | | | |
| V _{(BR)DSS} | drain-source | $I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ | 40 | - | - | V |
| | breakdown voltage | $I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$ | 36 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u> | 1.8 | 2.3 | 2.8 | V |
| | | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u> | - | - | 3.3 | V |
| | | I _D = 2.5 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 10</u> | 0.8 | - | - | V |
| DSS | drain leakage current | V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C | - | - | 500 | μΑ |
| | | $V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 0.02 | 1 | μΑ |
| GSS | gate leakage current | $V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ °C}$ | - | 2 | 100 | nA |
| | | $V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$ | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u> | - | 1.6 | 1.9 | mΩ |
| | | V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u> | - | 2 | 2.6 | mΩ |
| | | V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u> | - | 2.25 | 3.1 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 11</u> | - | - | 4 | mΩ |
| Dynamic ch | aracteristics | | | | | |
| Q _{G(tot)} total gate charge | | I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V; see <u>Figure 13</u> ; see <u>Figure 14</u> | - | 260 | - | nC |
| | | I _D = 25 A; V _{DS} = 32 V; V _{GS} = 5 V; see <u>Figure 13</u> ; see <u>Figure 14</u> | - | 147 | - | nC |
| Q _{GS} | gate-source charge | $I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$ | - | 38 | - | nC |
| Q _{GD} | gate-drain charge | see Figure 13; see Figure 14 | - | 72 | - | nC |
| C _{iss} | input capacitance | $V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$ | - | 11.3 | 15.1 | nF |
| C _{oss} | output capacitance | $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{1000}$ | - | 1447 | 1750 | pF |
| C _{rss} | reverse transfer capacitance | | - | 1014 | 1390 | pF |
| d(on) | turn-on delay time | $V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$ | - | 60 | - | ns |
| r | rise time | $R_{G(ext)} = 10 \ \Omega$ | - | 140 | - | ns |
| d(off) | turn-off delay time | | - | 234 | - | ns |
| f | fall time | | - | 416 | - | ns |
| -D | internal drain inductance | from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ °C}$ | - | 3.5 | - | nH |
| Ls | internal source inductance | from source lead to source bond pad; $T_i = 25 ^{\circ}\text{C}$ | - | 7.5 | - | nH |

Table 6.

Symbol

Characteristics ... continued

Parameter

Conditions

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Max

Unit

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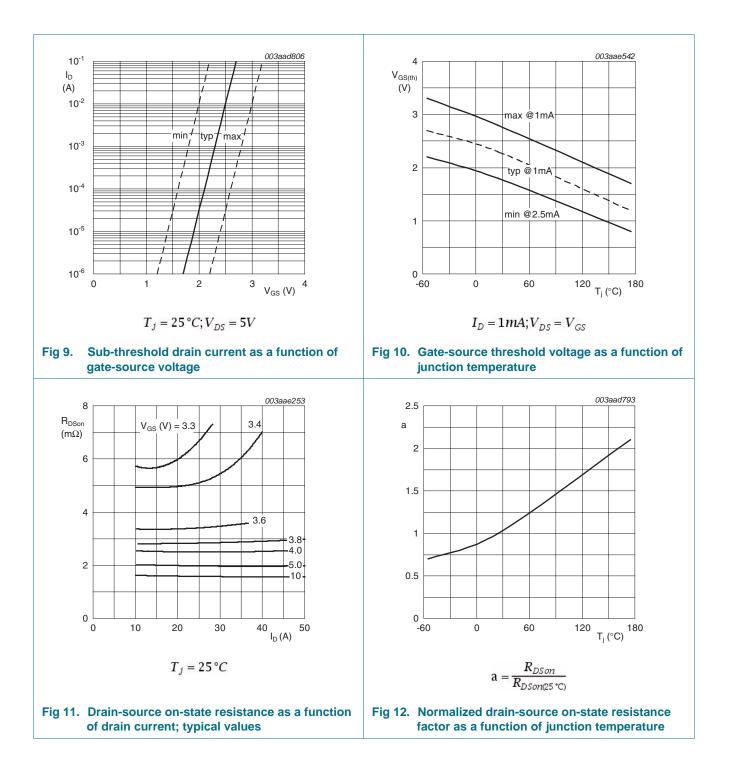
Тур

Min

| Source-dra | | | | | | |
|--|---|--|--|--------------------------------|------------------------|--------|
| / _{SD} | source-drain voltage | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 15</u> | - | 0.8 | 1.2 | V |
| r | reverse recovery time | $I_{S} = 20 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu s; V_{GS} = 0 \text{ V};$ | - | 63 | - | ns |
| 2 _r | recovered charge | V _{DS} = 25 V | - | 127 | - | nC |
| | | 003aae251 | | (| 003aae250 | |
| 250 g _{fs} (S) 200 | | R _{DSon} (mΩ) | | | | |
| 150 - | | 6 | | | | |
| 100 | | | | | | |
| 50 | | 2 | | | | |
| م م م | 20 40 60 | 80 _{I_D(A)} 100 0 0 | 5 10 | 15 | 20 V _{GS} (V) | |
| | | | | | • 65 (•) | |
| | $T_j = 25 ^{\circ}C; V_{DS} = 10$ | | $T_j = 25 ^{\circ}C; I_D =$ | | · GS (· / | |
| | $T_j = 25 ^{\circ}C; V_{DS} = 10$ prward transconductance a ain current; typical values | ₩ As a function of Fig 6. Drain-sou | $T_j = 25 ^{\circ}C; I_D =$ since on-state repurce voltage; t | = 25A esistanc | e as a fu | unctio |
| 100 | orward transconductance a | <i>V</i> as a function of Fig 6. Drain-sou of gate-so | Irce on-state re | = 25A esistanc typical v | e as a fu | unctio |
| dra | orward transconductance a ain current; typical values | V Fig 6. Drain-sou 003aae248 003aae248 | Irce on-state re | = 25A esistanc typical v | e as a fu /alues. | unctio |
| 100 I _D (A) | orward transconductance a ain current; typical values | OV Fig 6. Drain-sou of gate-so 003aae248 80 3.6- ID (A) 60 | Irce on-state re | = 25A esistanc typical v | e as a fu /alues. | unctio |
| 100 I _D (A) 80 | orward transconductance a ain current; typical values | OV Fig 6. Drain-sou of gate-so 003aae248 80 3.6- 10 3.6- 60 3.4- 40 | purce on-state re purce voltage; t | = 25A | e as a fu /alues. | unctio |
| dra 100 I _D (A) 80 60 | prward transconductance a ain current; typical values | $\begin{array}{c c} & & & & \\ \hline & & $ | Irce on-state re | = 25A | e as a fu /alues. | unctio |
| dra 100 I _D (A) 80 60 40 | prward transconductance a ain current; typical values | 0V Fig 6. Drain-sou of gate-so 003aae248 $003aae248$ 3.6 $003aae248$ 3.6 $003aae248$ 003aae248 $000aae248$ 003aae248 $000aae248$ 003aae248 $000aae248$ 003aae248 $000aae248$ 000aae248 <td>purce on-state re purce voltage; t</td> <td>= 25A</td> <td>e as a fu</td> <td>unctio</td> | purce on-state re purce voltage; t | = 25A | e as a fu | unctio |
| dra 100 I _D (A) 80 60 40 20 0 | prward transconductance a ain current; typical values | Fig 6. Drain-sou of gate-so 003aae248 (A) | T _j = 175° | = 25A esistanc typical v | e as a fu values. | unctio |

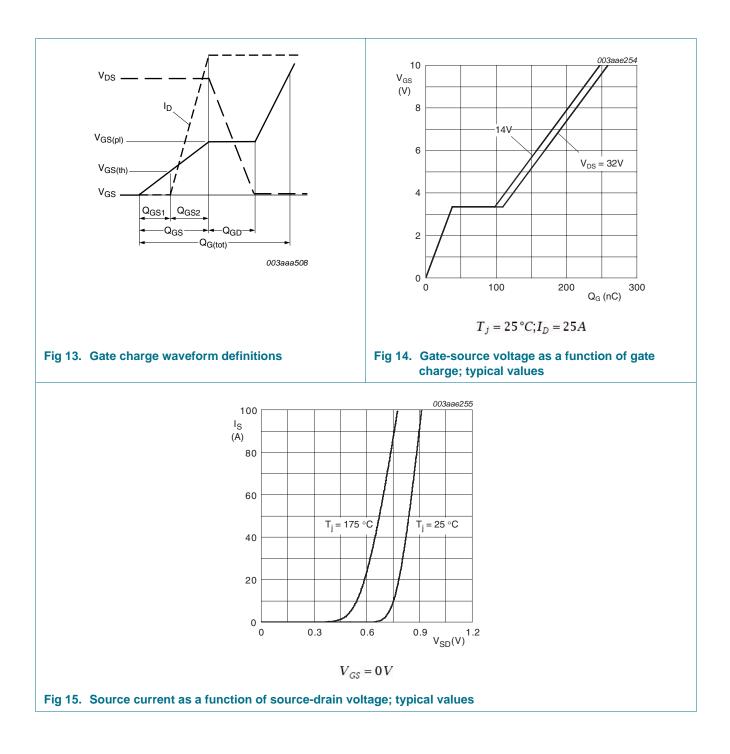
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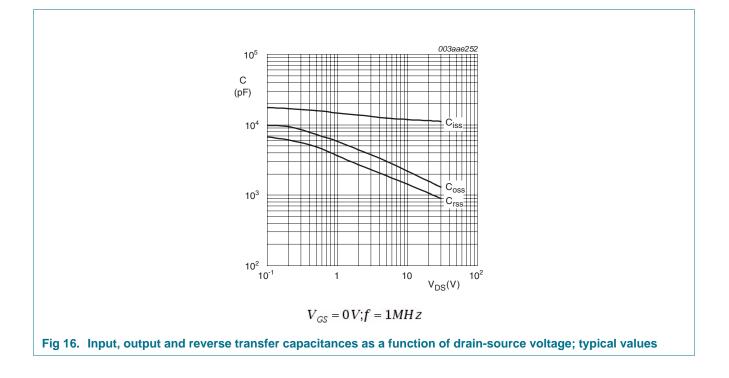
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7. Package outline

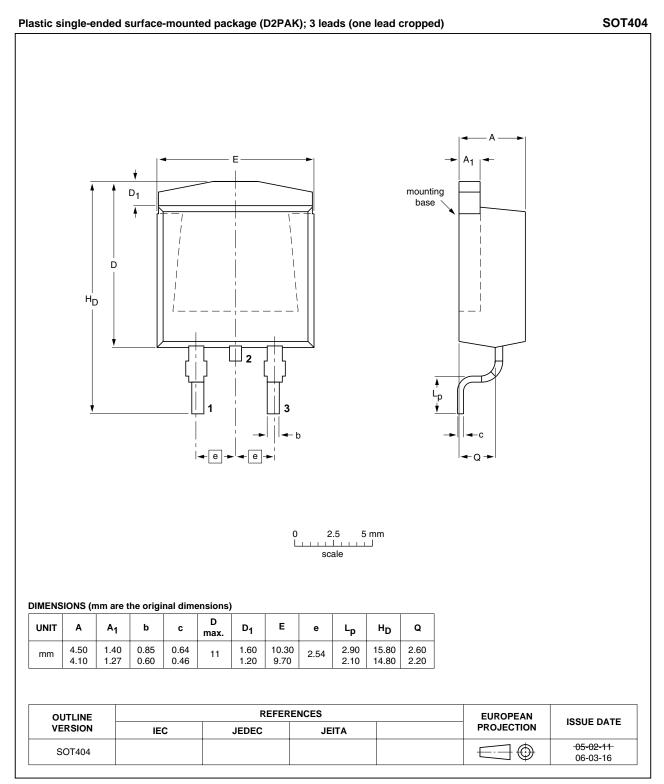


Fig 17. Package outline SOT404 (D2PAK)

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8. Revision history

| Table 7. Revision h | Revision history | | | | | | |
|---------------------|------------------|--------------------|---------------|------------|--|--|--|
| Document ID | Release date | Data sheet status | Change notice | Supersedes | | | |
| BUK661R9-40C v.1 | 20100818 | Product data sheet | - | - | | | |

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9. Legal information

9.1 Data sheet status

| Document status[1][2] | Product status ^[3] | Definition |
|--------------------------------|-------------------------------|---|
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